



SHENZHEN MENGKE ELECTRONICS TECHNOLOGY CO.,LTD

SOT-23 Plastic-Encapsulate MOSFETs**BSS84****P-Channel 50-V(D-S) MOSFET**

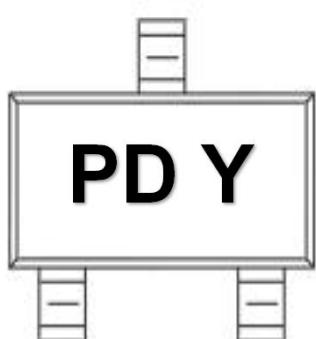
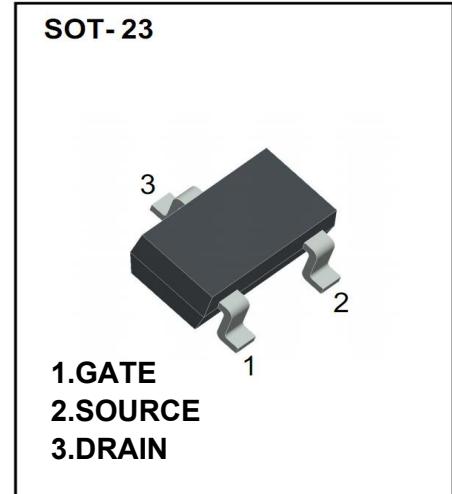
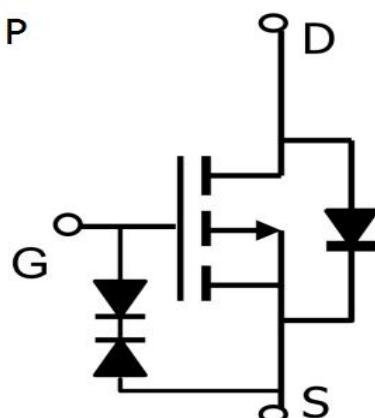
| V(BR)DSS | RDS(on)MAX | ID |
|--------------|----------------|---------------|
| -50 V | 4Ω@10V | -130mA |
| | 5Ω@4.5V | |

FEATURE:

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- Miniature Surface Mount Package Saves Board Space
- ESD Protected

APPLICATION:

※ DC-DC converters, load switching, power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

MARKING:**Equivalent Circuit:****Mosfet Maximum ratings (Ta=25°C unless otherwise noted)**

| Parameter | Symbol | Value | Unit |
|--|------------------|----------|------|
| Drain-Source Voltage | VDS | -50 | V |
| Gate-Source Voltage | VGS | ±20 | |
| Continuous Drain Current | ID | -130 | mA |
| Pulsed Drain Current (note 1) @tp <10 μs | IDM | -520 | |
| Power Dissipation | PD | 225 | mW |
| Thermal Resistance from Junction to Ambient | R _{θJA} | 556 | °C/W |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{STG} | -55~+150 | °C |
| Maximum Lead Temperature for Soldering Purposes , Duration for 5 Seconds | TL | 260 | °C |

**MOSFET ELECTRICAL CHARACTERISTICS****unless otherwise specified Ta = 25 °C**

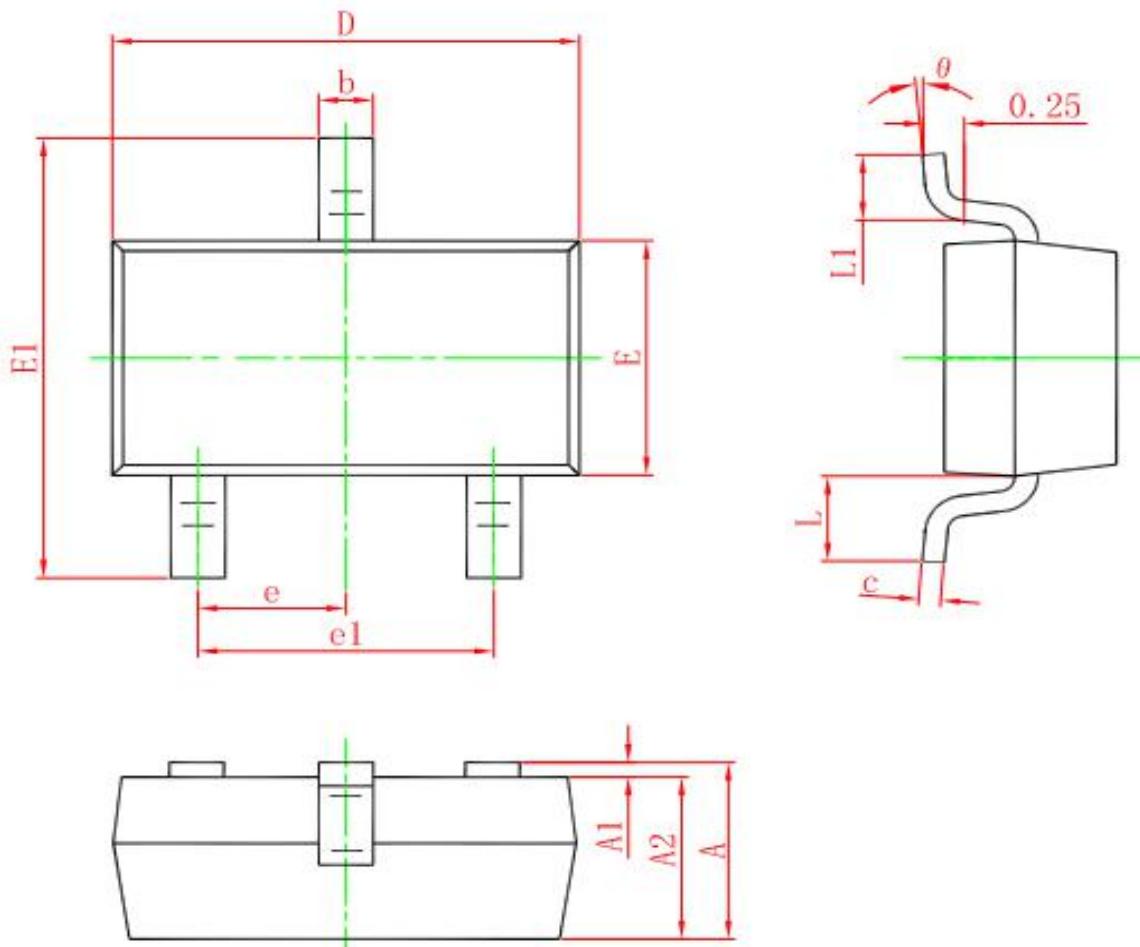
| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|---|----------|---------------------------------|-----|------|-------|------|
| Static Characteristics | | | | | | |
| Drain-source breakdown voltage | V(BR)DSS | VGS = 0V, ID = -250µA | -50 | | | V |
| Gate-threshold voltage | VGS(th) | VDS = VGS, ID = -250µA | -1 | | -2 | V |
| Gate-body leakage | IGSS | VDS = 0V, VGS = ±20V | | | ±10 | µA |
| Zero gate voltage drain current | IDSS | VDS = -50V, VGS = 0V | | | -15 | µA |
| Drain-source on-resistancea | RDS(on) | VGS = -10V, ID = -100mA | | 1.9 | 4 | Ω |
| | | VGS = -4.5V, ID = -100mA | | 2.4 | 5 | Ω |
| Forward transconductancea | gfs | VDS = -10V, ID = -100mA | 50 | | | S |
| Diode forward voltage | VSD | IS= -0.13A, VGS=0V | | -0.8 | -1.3 | V |
| Dynamic Characteristics | | | | | | |
| Input capacitance | Ciss | VDS = -5V, VGS = 0V, f=1MHz | | 30 | | pF |
| Output capacitance | Coss | | | 10 | | pF |
| Reverse transfer capacitanceb | Crss | | | 5 | | pF |
| Switchingb Characteristics | | | | | | |
| Turn-on delay time | td(on) | VDD= -15V RL=5Ω, ID = -50mA, | | 2.5 | | ns |
| Rise time | tr | | | 1 | | ns |
| Turn-off delay time | td(off) | | | 16 | | ns |
| Fall time | tf | | | 8 | | ns |
| SOURCE-DRAIN DIODE CHARACTERISTICS | | | | | | |
| Continuous Current | IS | | | | -0.13 | A |
| Pulsed Current | ISM | | | | -0.52 | A |

Note :

- 1.Repetitive rating : Pulse width limited by junction temperature.
- 2.Surface mounted on FR4 board , t≤10s.
- 3.Pulse Test : Pulse Width≤300µs, Duty Cycle≤2%.
- 4.Guaranteed by design, not subject to producing.



SOT-23 PACKAGE OUTLINE DIMENSIONS



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.900 | 1.150 | 0.035 | 0.045 |
| A1 | 0.000 | 0.100 | 0.000 | 0.004 |
| A2 | 0.900 | 1.050 | 0.035 | 0.041 |
| b | 0.300 | 0.500 | 0.012 | 0.020 |
| c | 0.080 | 0.150 | 0.003 | 0.006 |
| D | 2.800 | 3.000 | 0.110 | 0.118 |
| E | 1.200 | 1.400 | 0.047 | 0.055 |
| E1 | 2.250 | 2.550 | 0.089 | 0.100 |
| e | 0.950 TYP. | | 0.037 TYP. | |
| e1 | 1.800 | 2.000 | 0.071 | 0.079 |
| L | 0.550 REF. | | 0.022 REF. | |
| L1 | 0.300 | 0.500 | 0.012 | 0.020 |
| theta | 0° | 8° | 0° | 8° |